

ABSTRACT

A semiconductor memory device includes a plurality of memory cell arrays, a plurality of redundant judgment circuits, and a redundant memory cell array. Each of the redundant judgment circuits is used for storing an address of a defective memory cell in the corresponding memory cell array and each of the redundant judgment circuits includes a block judgment unit which outputs a block judgment signal and an address judgment unit which outputs a redundant judgment signal. The block judgment unit outputs the block judgment signal when the corresponding memory cell array includes the defective memory cell. The address judgment unit outputs the redundant judgment signal when the block judgment signal is outputted from the block judgment unit and the address of the defective memory cell matches an external address.